HMC517LC4

v04.1017

SMT PHEMT LOW NOISE AMPLIFIER, 17 - 26 GHz

Typical Applications

The HMC517LC4 is ideal for use as a LNA or driver amplifier for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- Test Equipment and Sensors
- Military

Features

Noise Figure: 2.5 dB

Gain: 19 dB

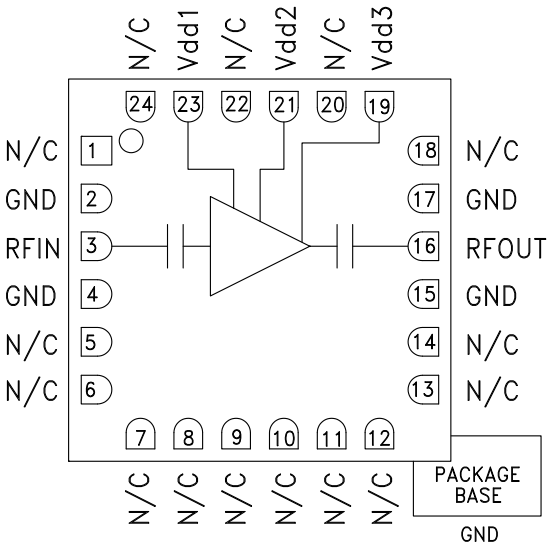
OIP3: +23 dBm

Single Supply: +3V @ 67 mA

50 Ohm Matched Input/Output

RoHS Compliant 4 x 4 mm Package

Functional Diagram



General Description

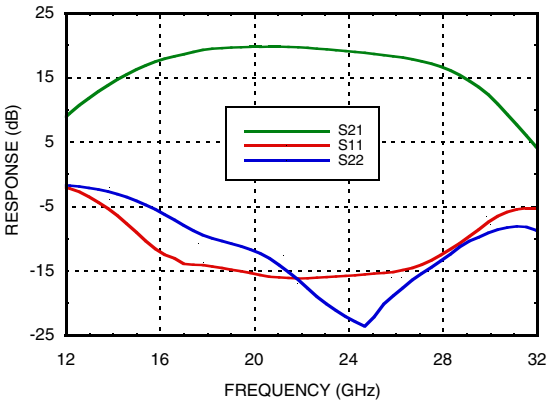
The HMC517LC4 chip is a high dynamic range GaAs pHEMT MMIC Low Noise Amplifier (LNA) housed in a leadless “Pb free” RoHS compliant SMT package. The HMC517LC4 provides 19 dB of small signal gain, 2.5 dB of noise figure and has an output IP3 of +23 dBm. The P1dB output power of +13 dBm enables the LNA to also function as a LO driver for balanced, I/Q or image reject mixers. The HMC517LC4 allows the use of surface mount manufacturing techniques.

Electrical Specifications, T_A = +25° C, Vdd 1, 2, 3 = +3V

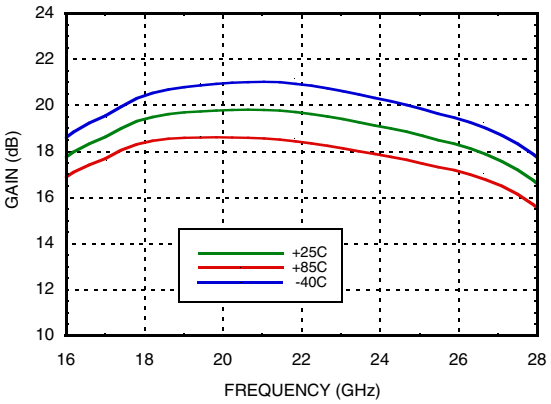
Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range		17 - 22			22 - 26		GHz
Gain	16	19		15	18		dB
Gain Variation Over Temperature		0.02	0.03		0.02	0.03	dB/ °C
Noise Figure		2.5	3.1		2.6	3.3	dB
Input Return Loss		15			15		dB
Output Return Loss		11			17		dB
Output Power for 1 dB Compression (P1dB)		12			13		dBm
Saturated Output Power (Psat)		15			16		dBm
Output Third Order Intercept (IP3)		23			24		dBm
Supply Current (Idd)(Vdd = +3V)		67			67		mA

For price, delivery, and to place orders: Analog Devices, Inc., One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106
Phone: 781-329-4700 • Order online at www.analog.com
Application Support: Phone: 1-800-ANALOG-D

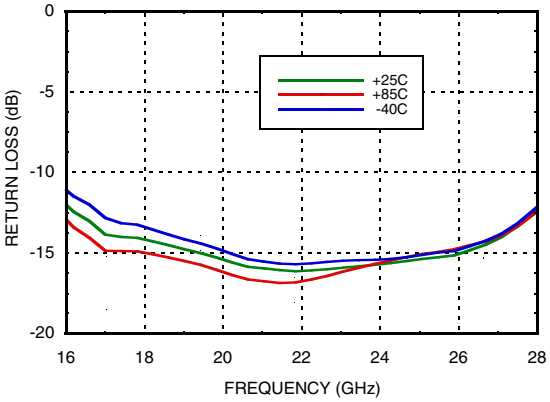
Broadband Gain & Return Loss



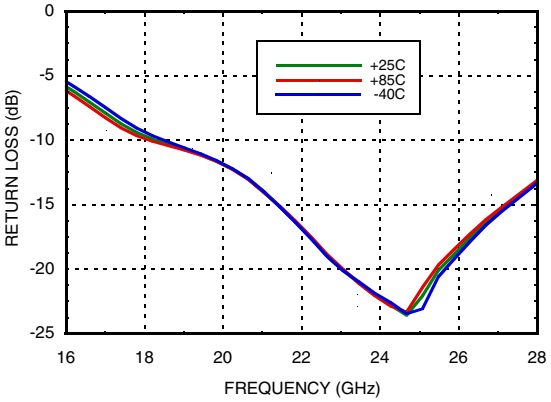
Gain vs. Temperature



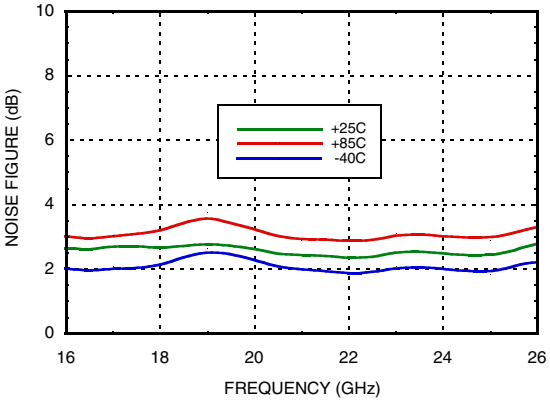
Input Return Loss vs. Temperature



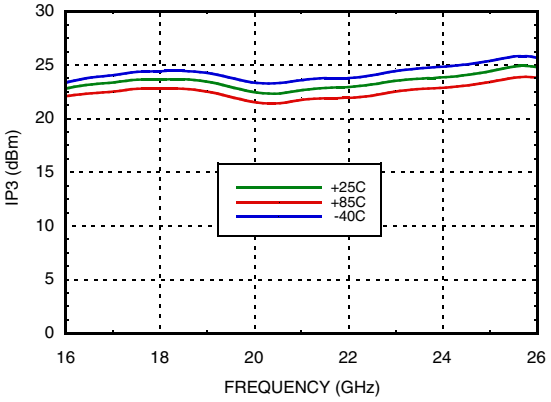
Output Return Loss vs. Temperature



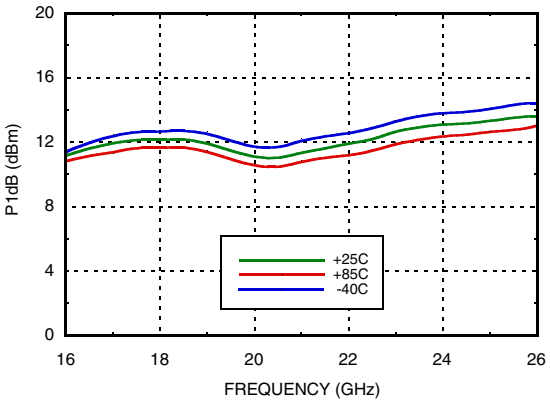
Noise Figure vs. Temperature



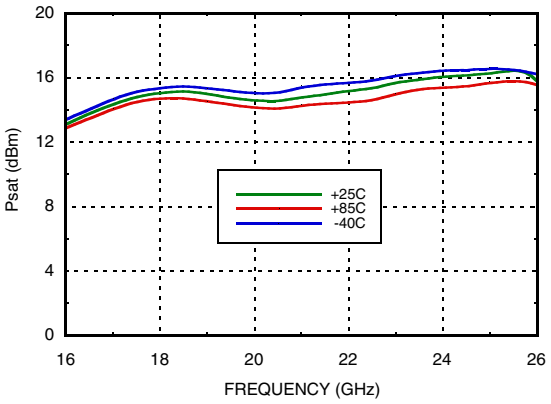
Output IP3 vs. Temperature



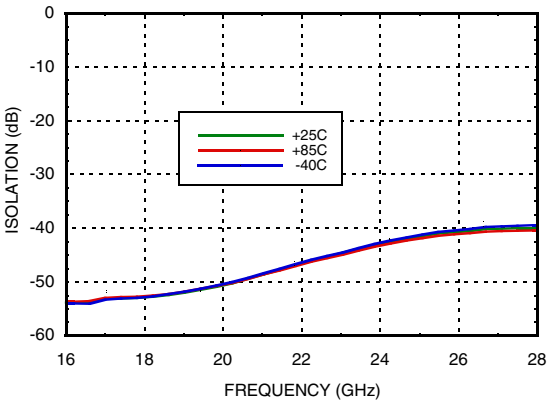
P1dB vs. Temperature



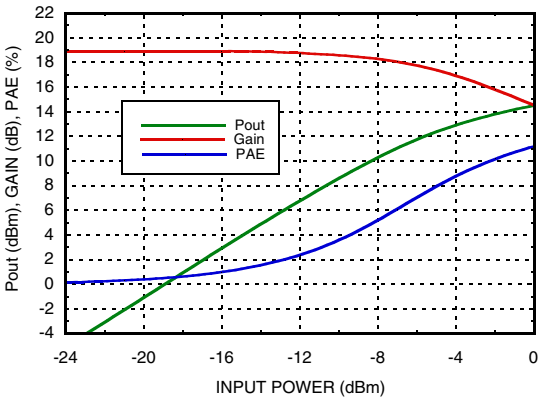
Psat vs. Temperature



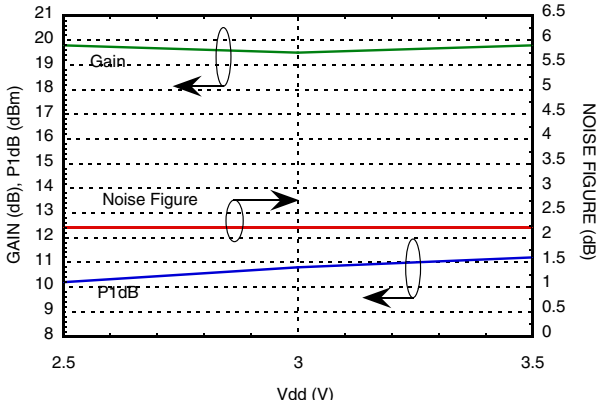
Reverse Isolation vs. Temperature



Power Compression @ 21 GHz



Gain, Noise Figure & Power vs. Supply Voltage @ 21 GHz



Absolute Maximum Ratings

Drain Bias Voltage (Vdd1, Vdd2, Vdd3)	+5.5 Vdc
RF Input Power (RFIN)(Vdd = +3.0 Vdc)	+14 dBm
Channel Temperature	175 °C
Continuous Pdiss (T= 85 °C) (derate 13 mW/°C above 85 °C)	1.2 W
Thermal Resistance (channel to die bottom)	76.9 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

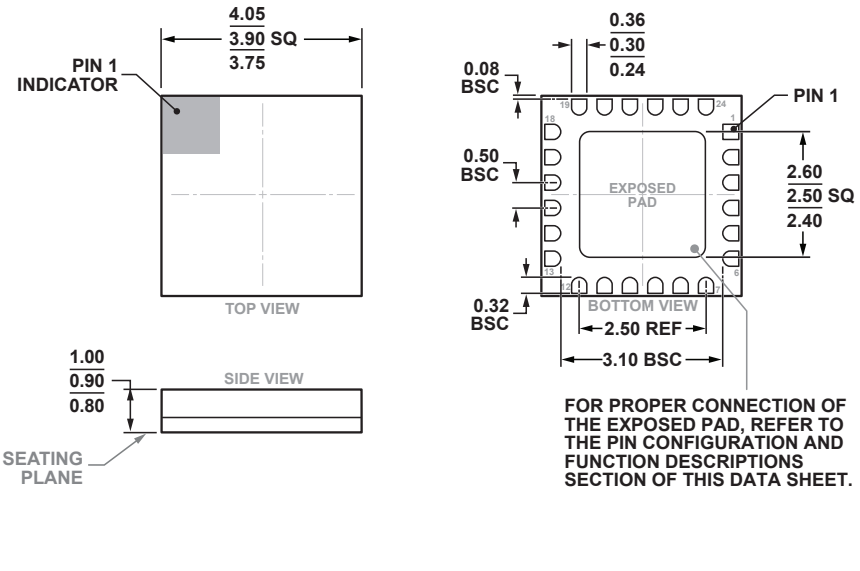
Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
+2.5	66
+3.0	68
+3.5	71

Note: Amplifier will operate over full voltage range shown above.

ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



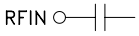
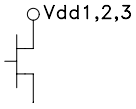
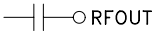
24-Terminal Ceramic Leadless Chip Carrier [LCC]
(E-24-1)
Dimensions shown in millimeters.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [2]
HMC517LC4	Alumina, White	Gold over Nickel	MSL3 [1]	H517 XXXX

[1] Max peak reflow temperature of 260 °C
[2] 4-Digit lot number XXXX

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 5 - 14, 18, 20, 22, 24	N/C	This pin may be connected to RF/DC ground. Performance will not be affected.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	
23, 21, 19	Vdd1, 2, 3	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1,000 pF and 2.2 µF are required.	
16	RFOUT	This pin is AC coupled and matched to 50 Ohms.	
2, 4, 15, 17	GND	These pins and package bottom must be connected to RF/DC ground.	

Application Circuit

Component	Value
C1, C2, C3	100 pF
C4, C5, C6	1,000 pF
C7, C8, C9	2.2 µF